

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A voltage driver circuit for driving a device at a selected one of a plurality of voltages associated with respective device operations including a high voltage operation and a relatively lower voltage operation, the driver circuit comprising an input (IN), a single output (OUT) for connection to said device, and a plurality of voltage drivers between said input and said output including ~~at least one a~~ high voltage breakdown driver and ~~at least one a~~ relatively lower breakdown voltage driver, wherein said high voltage breakdown driver comprises inverters and said relatively lower breakdown voltage driver comprises an inverter, wherein an output of one of the inverters of said high voltage breakdown driver is connected to an input of the inverter of said relatively lower breakdown voltage driver, the circuit being arranged such that, during a high voltage operation, said high voltage breakdown driver is connected to said output and there is a substantially zero voltage drop across said relatively lower breakdown voltage driver, and, during a relatively lower voltage operation, said relatively lower breakdown voltage driver provides the drive voltage for driving said device, the contribution of said high breakdown voltage driver to said drive voltage during said relatively lower voltage operation being substantially negligible.

2. (currently amended) A circuit according to claim 1, wherein ~~the high voltage breakdown drivers comprise the inverters of said high voltage breakdown driver consisting~~ consist of high voltage breakdown transistors.

3. (currently amended) A circuit according to claim-2, wherein ~~the at least one relatively lower breakdown voltage driver comprises an~~ the inverter of said relatively

lower breakdown voltage driver ~~consisting~~ consists of relatively lower breakdown voltage transistors.

4. (previously presented) A circuit according to claim 1, comprising two signal paths between the input and the output, a first signal path consisting of one or more high voltage drivers connected in series, and a second signal path consisting of at least one low voltage driver, the first and second signal paths being connected in parallel to one another.

5. (original) A circuit according to claim 4, comprising means for selecting the first signal path during high voltage operation.

6. (currently amended) A voltage driver circuit for driving a device at a selected one of a plurality of voltages associated with respective device operations including a high voltage operation and a relatively lower voltage operation, the driver circuit comprising an input (IN), a single output (OUT) for connection to said device, and a plurality of voltage drivers between said input and said output including ~~at least one a~~ high voltage breakdown driver and ~~at least one a~~ relatively lower breakdown voltage driver, wherein the high breakdown voltage driver comprises ~~comprising~~ a voltage level shifter that which is connected at the input of the circuit that is between first and second voltage lines, and the relatively lower breakdown voltage driver comprises ~~an inverter~~, wherein the an output of said voltage level shifter being is connected to the an input of the inverter of the a relatively lower breakdown voltage driver and the inverter of the relatively lower breakdown voltage driver is connected to the single output between said first and second voltage lines, the voltage driver circuit being arranged such that, during a high voltage operation, there is a substantially zero voltage drop across said relatively lower breakdown voltage driver.

7. (original) A circuit according to claim 6, whercin said voltage level shifter comprises a partial level shifter.

8. (currently amended) A circuit according to claim 6 wherein the relatively lower breakdown voltage driver comprises an inverter of said relatively lower breakdown voltage driver consists of thick gate oxide devices.

9. (previously presented) A circuit according to claim 8, wherein the thick gate oxide devices comprise GO_2 devices.

10. (currently amended) A circuit according to claim 6, wherein said at least one relatively lower breakdown voltage driver comprises an I/O protection inverter.

11. (previously presented) A circuit according to claim 6, wherein a high voltage pull-up or pull-down transistor is provided between the output and the first or second voltage lines respectively.

12. (previously presented) A memory device, comprising a voltage driver circuit according to claim 1.

13. (original) An integrated circuit, comprising or including a memory device according to claim 12.

14. (original) A computing system, including an integrated circuit according to claim 13.

15. (new) A circuit according to claim 3, wherein source electrodes of some high voltage breakdown transistors and a source electrode of a first relatively lower breakdown voltage transistor are connected to a first voltage line, wherein source electrodes of some other high voltage breakdown transistors and a source electrode of a second relatively lower breakdown voltage transistor are connected to a second voltage line.

16. (new) A circuit according to claim 8, wherein the voltage level shifter comprises transistors, wherein source electrodes of some transistors of the voltage level shifter and a

source electrode of a first thick gate oxide device are connected to the first voltage line, wherein source electrodes of some other transistors of the voltage level shifter and a source electrode of a second thick gate oxide device are connected to the second voltage line.